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(54) SEMICONDUCTOR STRUCTURE AND METHOD OF MAKING THE SAME

(71) Applicant: ChangXin Memory Technologies, Inc., Hefei City (CN)

Inventors: Tieh-Chiang Wu, Hefei City (CN); Lingxin Zhu, Hefei City (CN)

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(57)**ABSTRACT**

A semiconductor structure and a method making it are disclosed. The method includes: providing a substrate, and sequentially forming a bitline contact structure and a bitline on the substrate; the bitline includes a connection layer connected to the bitline contact structure. The bitline contact structure and the sidewalls of the connection layer are etched back. A first silicide layer covering the sidewalls of the bitline contact structure, and a second silicide layer covering the sidewalls of the connection layer are formed. This structure can reduce the contact resistance between the bitline contact structure and the bitline, as well as the parasitic capacitance between the bitline contact structure and the adjacent conductive structures, thereby improving the electrical performance and reliability of the semiconductor structure and improving the semiconductor yield.

